a substrate;

a plurality of scanning lines;

a plurality of data lines, one of the data lines crossing one of the plurality of scanning lines; and

a plurality of transistors disposed correspondingly to intersections between the plurality of data lines and the plurality of scanning lines,

each of the plurality of transistors comprising:

a gate electrode; and

a semiconductor having a channel region and at least one portion extending outside of the channel region in a gate-width direction perpendicular to a gate-length direction that is a direction in which one of the plurality of data lines extends,

the at least one portion and at least one of a source region and a drain region being separated by an extension of the gate electrode, and the extension extending in the gate-length direction outside of the semiconductor region.

8. (Amended) An electronic equipment, comprising:

a light source;

the electro-optical device according to claim 1 that modulates, in accordance with image information, an incident light emitted by the light source; and

a projection system that projects a light modulated by the electro-optical device.

Please add new claims 21-23 as follows:

--21. A thin-film-transistor array substrate, comprising:

a substrate;

a plurality of scanning lines;

a plurality of data lines, one of the data lines crossing one of the plurality of scanning lines; and

a plurality of transistors disposed correspondingly to intersections between the plurality of data lines and the plurality of scanning lines,

each of the plurality of transistors further comprising:

a gate electrode; and

a semiconductor having a channel region and at least one portion extending outside of the channel region in a gate-width direction perpendicular to a gate-length direction that is a direction in which one of the plurality of data lines extends,

the at least one portion and at least one of a source region and a drain region being separated by an extension of the gate electrode.--

--22. A electro-optical device, comprising:

a substrate;

a plurality of scanning lines;

a plurality of data lines, one of the data lines crossing one of the plurality of scanning lines; and

a plurality of transistors disposed correspondingly to intersections between the plurality of data lines and the plurality of scanning lines,

each of the plurality of transistors further comprising:

a gate electrode; and

a semiconductor having a channel region and at least one portion extending outside of the channel region in a gate-width direction perpendicular to a gate-length direction that is a direction in which one of the plurality of data lines extends,

the at least one portion and at least one of a source region and a drain region being separated by an extension of the gate electrode.--